

**ABSTRACT OF THE DISCLOSURE**

A method of producing a silicon carbide single crystal has  
storing a sublimation law material on a first end portion  
5 in a reaction container;

disposing a seed crystal of a silicon carbide single crystal  
on a second end portion substantially facing the sublimation  
law material in the reaction container; and

re-crystallizing the sublimated sublimation law material  
10 on the seed crystal to grow a silicon carbide single crystal,  
wherein a sealing portion is provided in the reaction  
container to grow a silicon carbide single crystal on the seed  
crystal provided in the sealing portion while preventing the  
leak of the sublimated sublimation law material from the  
15 atmosphere for sublimation.